

SSC8131GS6

P-Channel Enhancement Mode MOSFET

> Features

VDS	VGS	RDSON Typ.	ID
-30V	±12V	45mR@-10V	
		52mR@-4V5	-4A
		63mR@-2V5	

> Description

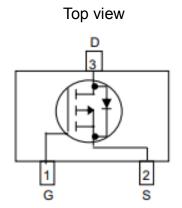
This device is particularly suited for low voltage application such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. Excellent thermal and electrical capabilities.

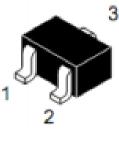
- > Applications
- Load Switch
- Portable Devices
- DCDC conversion

> Ordering Information

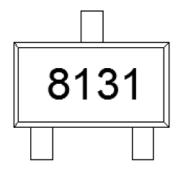
Device	Package	Shipping
SSC8131GS6	SOT23	3000/Reel

> Pin configuration





SOT23



Marking



> Absolute Maximum Ratings(T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V _{DSS}	Drain-to-Source Voltage	-30	V	
V_{GSS}	Gate-to-Source Voltage	±12	V	
I _D	Continuous Drain Current ^a	-4	А	
I _{DM}	Pulsed Drain Current ^b	-15	А	
PD	Power Dissipation ^c	1.35	W	
P _{DSM}	Power Dissipation ^a	0.8	W	
TJ	Operation junction temperature -55 to 150		°C	
T _{STG}	Storage temperature range	-55 to 150	°C	

➤ Thermal Resistance Ratings(T_A=25°C unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{ extsf{ heta}JA}$	Junction-to-Ambient Thermal Resistance ^a		160	°C/W
$R_{ extsf{ heta}JC}$	Junction-to-Case Thermal Resistance		95	C/ W

Note:

- a. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with T_A=25C°. The value in any given application depends on the user is specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

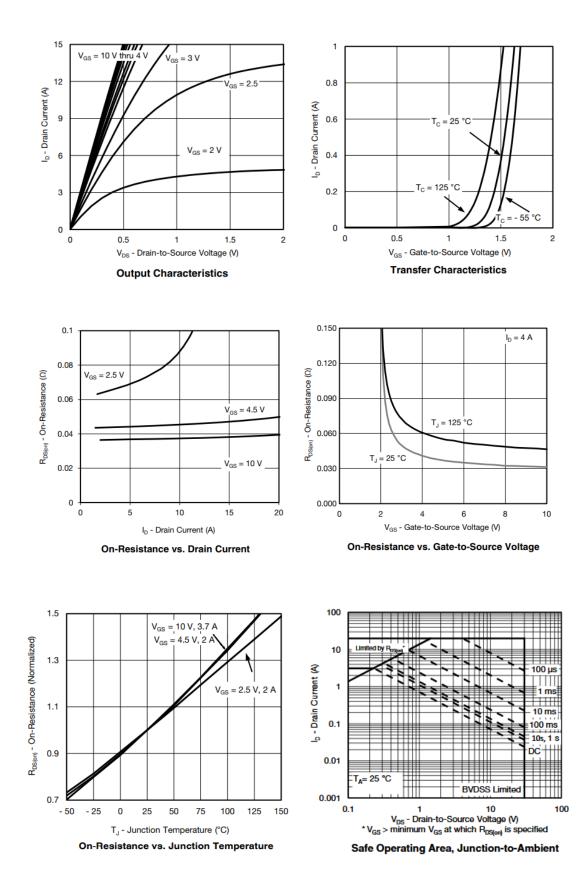


Electronics Characteristics(T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Мах	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	-30			V
$V_{GS \ (th)}$	Gate Threshold Voltage	VDS=VGS , ID=-250uA	-0.6	-0.7	-1.1	V
R _{DS(on)}	Drain-Source On- Resistance	VGS=-10V , ID=-4A		45	58	mR
		VGS=-4.5V , ID=-2A		52	61	
		VGS=-2.5V , ID=-1A		63	71	
I _{DSS}	Zero Gate Voltage Drain Current	VDS=-30V , VGS=0V			-1	uA
I _{GSS}	Gate-Source leak current	VGS=±12V , VDS=0V			±100	nA
G _{FS}	Transconductance	VDS=-5V , ID=-3A		10		S
V_{SD}	Forward Voltage	VGS=0V , IS=-1A		-0.7	-1.3	V
Ciss	Input Capacitance			600		
Coss	Output Capacitance	VDS=-15V , VGS=0V , f=1MHz		85		pF
Crss	Reverse Transfer Capacitance			66		
T _{D(ON)}	Turn-on delay time	VGS=-6V, VGEN=-4.5V, RL=6R, RG=6R ,ID=-1.0A		13		
Tr	Rise time			18		ns
$T_{D(OFF)}$	Turn-off delay time			40		
Tf	Fall time			8		

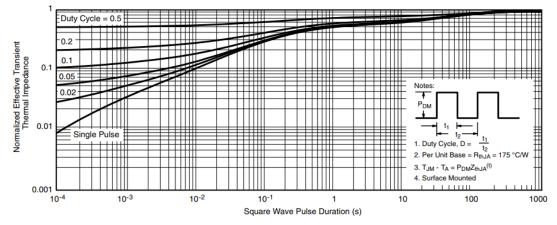


> Typical Characteristics(T_A=25°C unless otherwise noted)





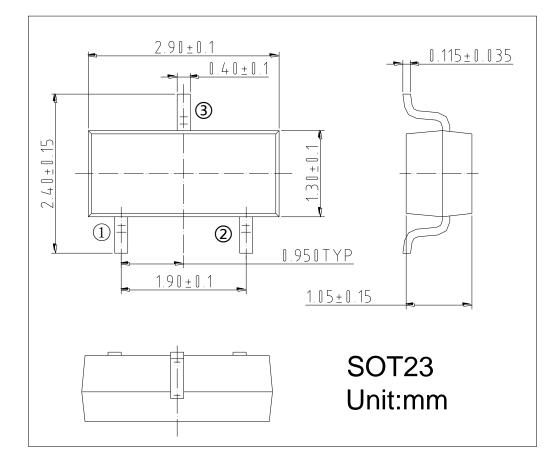
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Normalized Thermal Transient Impedance, Junction-to-Ambient



> Package Information



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